

## Supplementary Information

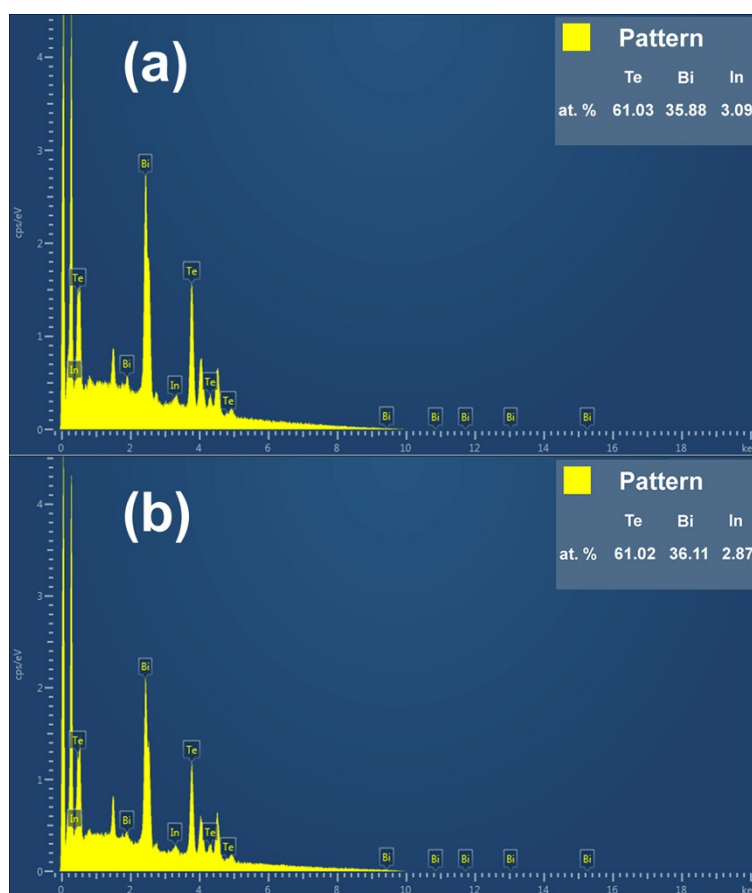
### Effect of doped indium into $\text{Bi}_2\text{Te}_3$ matrix on the microstructure and thermoelectric transport properties

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**Fig. S1.** EDS patterns and atomic ratios of A (a) and B (b) regions in Fig.2(c) of the article.

**Table S1.** The atomic ratios analysis of as-prepared samples via EDS measurement.

Nominal composition	Elemental composition		
	In (at. %)	Bi (at. %)	Te (at. %)
$\text{Bi}_{1.95}\text{In}_{0.05}\text{Te}_3$	1.02	40.21	58.77
$\text{Bi}_{1.93}\text{In}_{0.07}\text{Te}_3$	1.45	39.48	59.07
$\text{Bi}_{1.9}\text{In}_{0.1}\text{Te}_3$	2.15	36.51	61.34
$\text{Bi}_{1.8}\text{In}_{0.2}\text{Te}_3$	3.98	36.92	59.10